## Amendments to the Specification

Please amend the paragraph beginning on line 10 of page 8 of the original specification as follows, where strike-through indicates the matter to be deleted and underline indicates the matter to be added:

Referring first to FIGS. 1 through 4, environmental conditions around the spinning wafer **W** impact the viscosity of the resist and its consequent thickness once it is deposited on the wafer. For semiconductor applications, a resist layer thickness is typically between approximately 0.1 and 1 micron. The relative dimensions of the wafer **W** and the resist ~~laye2~~ layer **100**, **300**, **400** and **500** disposed thereon shown in the figures are not to scale, but meant to show general trends in non-uniform resist layers in their as-deposited state. Solvents are initially a part of the resist solution, and are included to promote solution flowability and related deposition properties. Upon deposition and exposure to the ambient environment (such as air) **A** around the wafer **W**, the solvents evaporate. By controlling the rate of evaporation of solvent from the resist **R** as it is being deposited, embodiments of the present invention promote improvements in resist layer thickness uniformity relative to that shown in FIGS. 1 through 4. Because viscosity is generally inversely proportional to the amount of solvent in the resist, the evaporation process (which has a strong influence over how much solvent remains in the resist), if extremely high, can inhibit the tendency of the resist to level out during subsequent layer deposition. This leads to surface undulations such as shown in FIGS. 1 through 4 where, depending on the processing and environmental conditions, differing thicknesses are produced at the resist layer center **C** from the periphery **P** and the intermediate **I**. For example, extremely high viscosities have a tendency to yield the dome-like pattern shown in FIG. 2, while extremely low viscosities have a tendency to yield the bowl-like shape of FIG. 1.